

SK 25 KQ

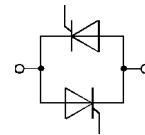
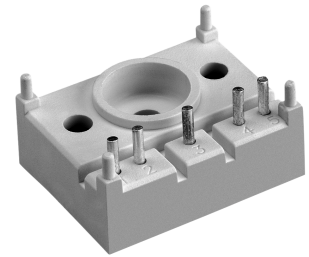
V_{RSM}	V_{RRM} V_{DRM}	I_{RMS} (maximum values for continuous operation) ($T_h = 85\text{ °C}$) 29 A
V	V	
900	800	SK 25 KQ 08
1300	1200	SK 25 KQ 12
1700	1600	SK 25 KQ 16

SEMITOP® 1

Antiparallel Thyristor Module

SK 25 KQ

Symbol	Conditions	Values	Units
I_{RMS}	W1C; sin 180°; $T_h = 100\text{ °C}$	20	A
	$T_h = 85\text{ °C}$	29	A
I_{TSM}	$T_{vj} = 25\text{ °C}$; 10 ms	320	A
	$T_{vj} = 125\text{ °C}$; 10 ms	280	A
i^2t	$T_{vj} = 25\text{ °C}$; 8,3...10 ms	510	A ² s
	$T_{vj} = 125\text{ °C}$; 8,3...10 ms	390	A ² s
t_{gd}	$T_{vj} = 25\text{ °C}$; $I_G = 1\text{ A}$; $di_G/dt = 1\text{ A}/\mu\text{s}$	1	μs
t_{gr}	$V_D = 0,67 V_{DRM}$	1	μs
$(dv/dt)_{cr}$	$T_{vj} = 125\text{ °C}$	500	V/ μs
$(di/dt)_{cr}$	$T_{vj} = 125\text{ °C}$; $f = 50\text{...}60\text{ Hz}$	100	A/ μs
t_q	$T_{vj} = 125\text{ °C}$; typ.	80	μs
I_H	$T_{vj} = 25\text{ °C}$; typ. / max	80 / 150	mA
I_L	$T_{vj} = 25\text{ °C}$; $R_G = 33\ \Omega$; typ. / max.	150 / 300	mA
V_T	$T_{vj} = 25\text{ °C}$; $I_T = 75\text{ A}$; max.	2,45	V
$V_{T(TO)}$	$T_{vj} = 125\text{ °C}$	1,10	V
r_T	$T_{vj} = 125\text{ °C}$	20	m Ω
I_{DD} ; I_{RD}	$T_{vj} = 125\text{ °C}$; $V_{DD} = V_{DRM}$, $V_{RD} = V_{RRM}$	max. 8	mA
V_{GT}	$T_{vj} = 25\text{ °C}$; dc	2	V
I_{GT}	$T_{vj} = 25\text{ °C}$; dc	100	mA
V_{GD}	$T_{vj} = 125\text{ °C}$; dc	0,25	V
I_{GD}	$T_{vj} = 125\text{ °C}$; dc	3	mA
$R_{thjh}^{1)}$	cont. per thyristor / per W1C	1,7 / 0,85	K/W
	sin 180° per thyristor / per W1C	1,78 / 0,89	K/W
T_{vj}	thyristor	- 40 ... + 125	°C
T_{stg}		- 40 ... + 125	°C
T_{solder}	terminals, 10 s	260	°C
V_{isol}	a.c. 50 Hz; r.m.s. 1 s/1 min	3000 / 2500	V~
M_1	mounting torque	1,5	Nm
w		13	g
Case		T 1	



KQ

Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- Glass passivated thyristor chips
- Up to 1600 V reverse voltage
- high surge currents
- UL recognized, file no. E 63 532

Typical Applications

- Soft starters
- Light control
- Temperature control

¹⁾ Thermal resistance junction to heatsink

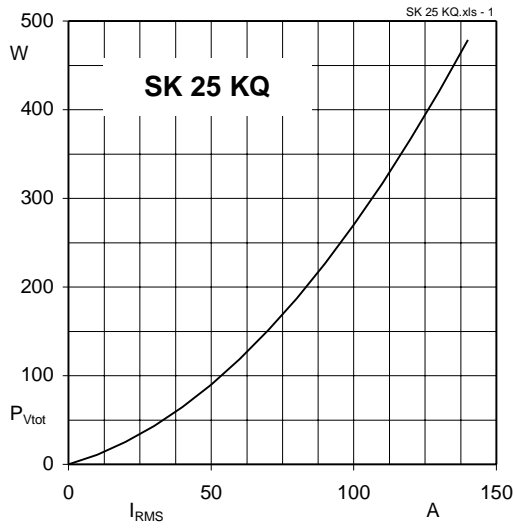


Fig. 1 Power dissipation per module vs. rms current

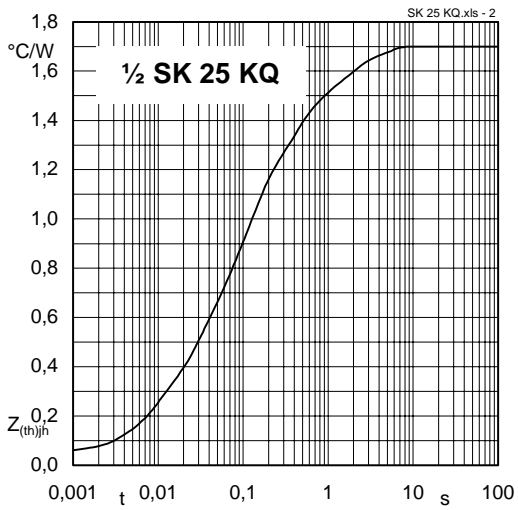


Fig. 2 Transient thermal impedance vs. time

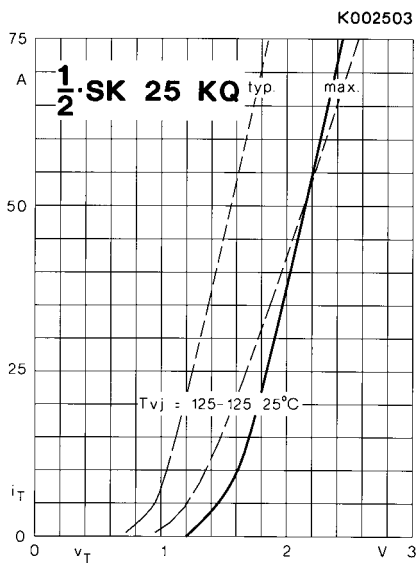


Fig. 3 On-state characteristics

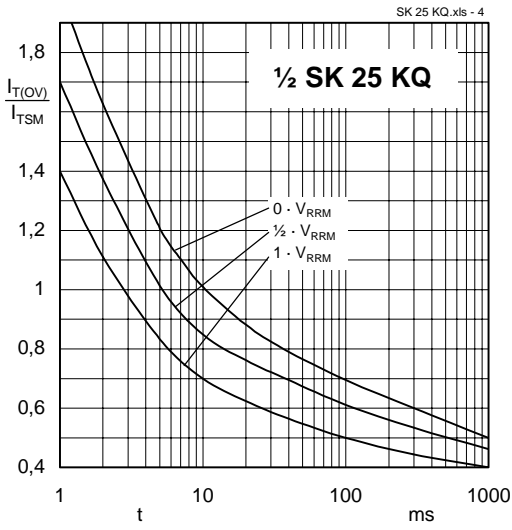


Fig. 4 Surge overload current vs. time

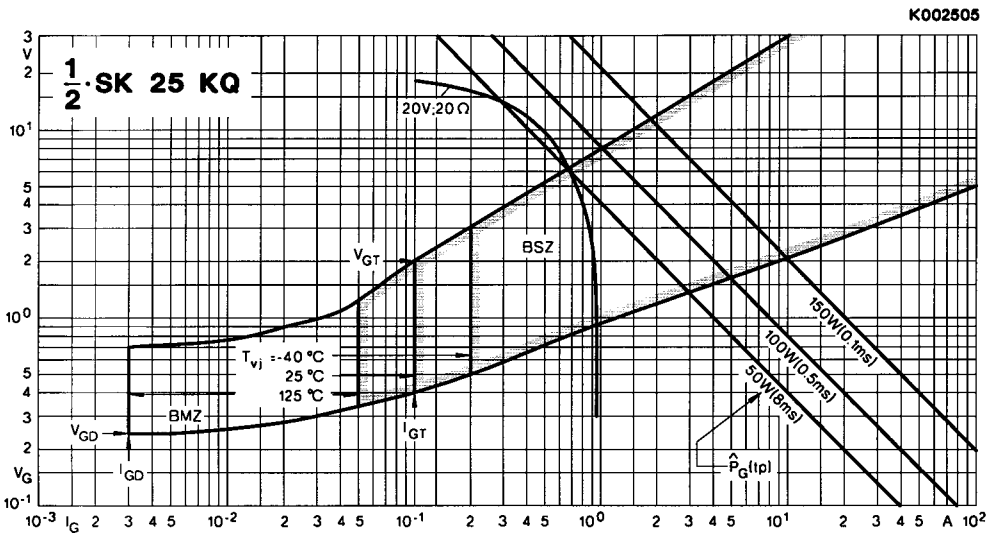
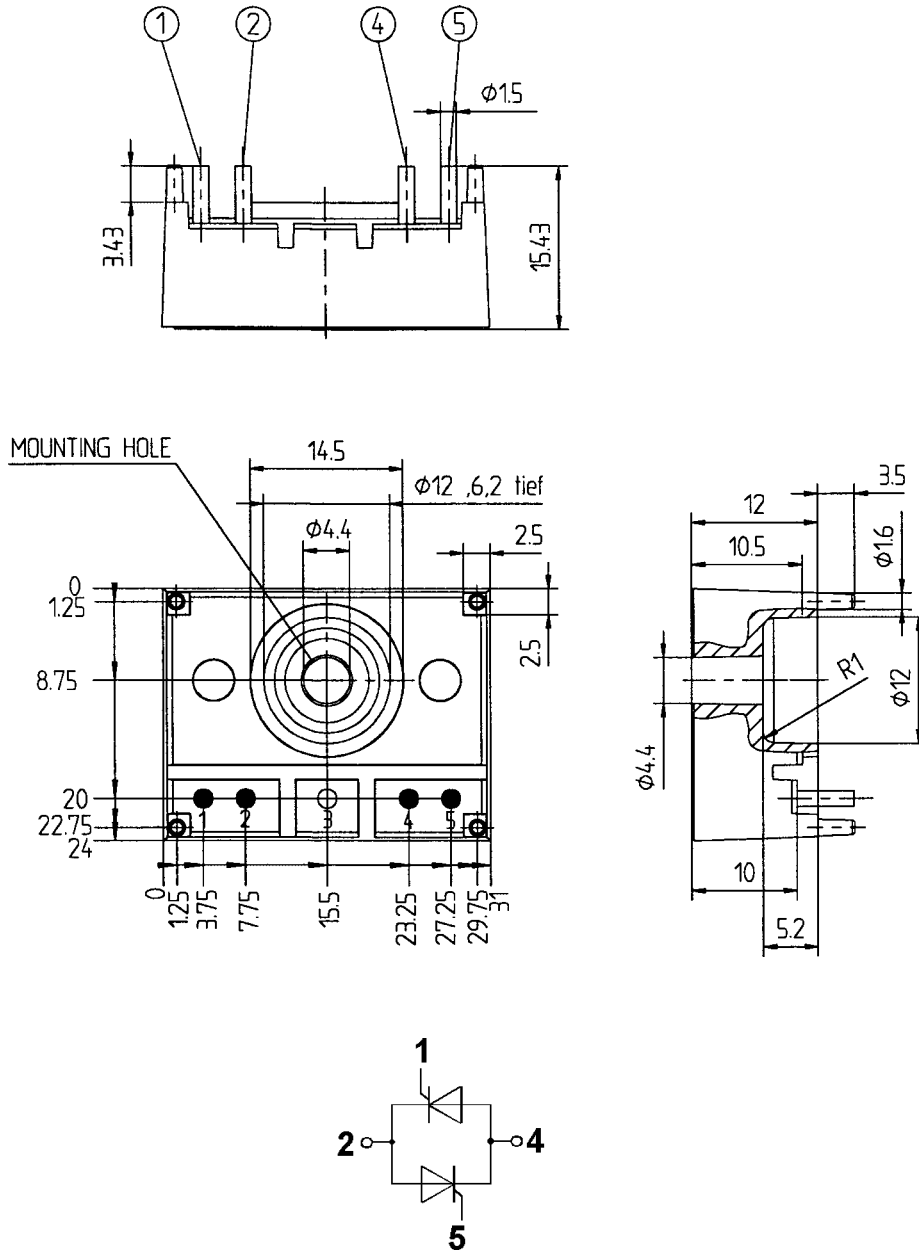


Fig. 5 Gate trigger characteristics

SEMITOP® 1
SK 25 KQ

Case T 1



Dimensions in mm

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